

What is claimed is:

1. A semiconductor device comprising:
an N type polysilicon gate and a P type polysilicon
gates both disposed simultaneously,
wherein a dummy gate made of non-doped polysilicon
for polysilicon gate etching is disposed in area larger
than the total area of the N type and P type polysilicon
gates.
2. The semiconductor device according to claim 1,
wherein impurities for the N type polysilicon gate and
the P type polysilicon gate are phosphor and boron
respectively.
3. A dry etching method for a semiconductor device,
comprising the following steps of:
simultaneously gate-etching an N type polysilicon
gate and a P type polysilicon gate; and
setting an etching area of a dummy gate made of
non-doped polysilicon for polysilicon gate etching larger
than the total area of the N type polysilicon gate and
the P type polysilicon gate to carry out said gate
etching.
4. The dry etching method according to claim 3,
wherein said gate etching is two-stage etching.

5. The dry etching method according to claim 4,
wherein the two-stage etching includes a first stage
using a mixed gas of HBr and O₂ and a second stage using a
mixed gas of HBr, O₂ and He.